

FDS6570A

Single N-Channel 2.5V Specified PowerTrench™ MOSFET

General Description

This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

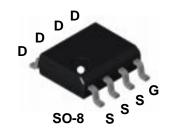
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

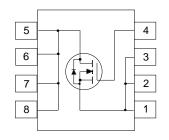
Applications

- DC/DC converter
- Load switch
- Battery protection

Features

- 15 A, 20 V. $R_{DS(on)} = 0.0075~\Omega~$ @ $V_{GS} = 4.5~V$ $R_{DS(on)} = 0.010~\Omega~$ @ $V_{GS} = 2.5~V.$
- Low gate charge (47nC typical).
- Fast switching speed.
- \bullet High performance trench technology for extremely low $R_{\mbox{\tiny DS(ON)}}.$
- High power and current handling capability.





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	FDS6570A	Units	
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		<u>±</u> 8	V
I _D	Drain Current - Continuous	(Note 1a)	15	Α
	- Pulsed		50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
T _J , T _{stg}	Operating and Storage Junction Temperature	-55 to +150	°C	

Thermal Characteristics

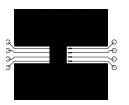
$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity	
FDS6570A	FDS6570A FDS6570A		12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			•		•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	20			V
<u>A</u> BVdss ΔTJ	Breakdown Voltage Temperature Coefficient	I _D = 250 _{LL} A, Referenced to 25°C		29		mV/∘C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 16 V, V _{GS} = 0 V			1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.4	0.9	1.5	V
ΔVGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to 25°C		-4		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 2.5 \text{ V}, I_D = 12 \text{ A}$		0.006 0.090 0.008	0.0075 0.0130 0.0100	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5.0 \text{ V}$	25			Α
g FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 15 \text{ A}$		70		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		4700		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		850		pF
C _{rss}	Reverse Transfer Capacitance			310		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$		20	32	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		27	44	ns
t _{d(off)}	Turn-Off Delay Time			95	133	ns
t _f	Turn-Off Fall Time			35	56	ns
Q _g	Total Gate Charge	$V_{DS} = 10 \text{ V}, I_{D} = 15 \text{ A},$		47	66	nC
$\overline{Q_gs}$	Gate-Source Charge	$V_{GS} = 5 V$,		7		nC
Q_{gd}	Gate-Drain Charge			10.5		nC
Drain-So	ource Diode Characteristics an	d Maximum Ratings				
I _S	Maximum Continuous Drain-Sou				2.1	А
$\overline{V_{SD}}$	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.1 A (Note 2)	İ	0.65	1.2	V

R_{BJA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design.







a) 50° C/W when mounted on a 0.5 in² pad of 2 oz. copper.

b) 105° C/W when mounted on a 0.02 in² pad of 2 oz. copper.

c) 125° C/W when mounted on a 0.003 in² pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%$

Typical Characteristics

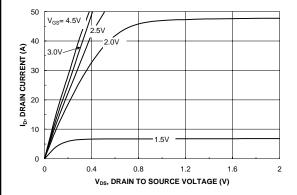
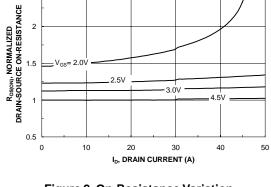


Figure 1. On-Region Characteristics.



2.5

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

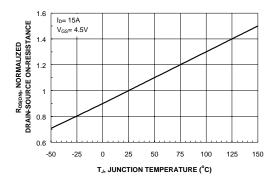


Figure 3. On-Resistance Variation with Temperature.

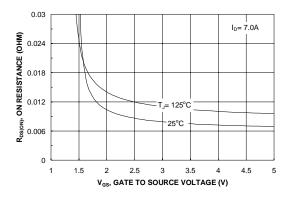


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

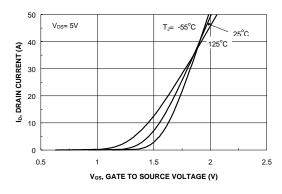


Figure 5. Transfer Characteristics.

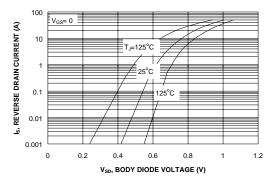
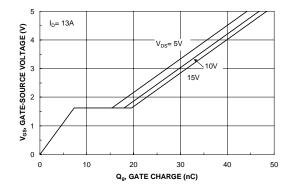


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



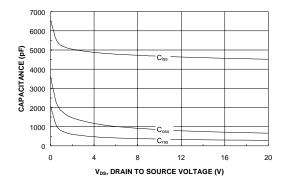
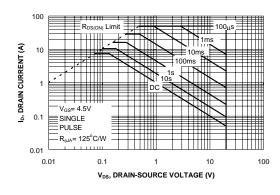


Figure 7. Gate Charge Characteristics.





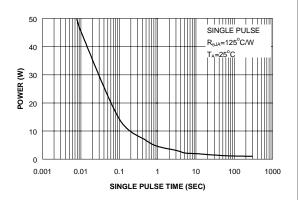


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

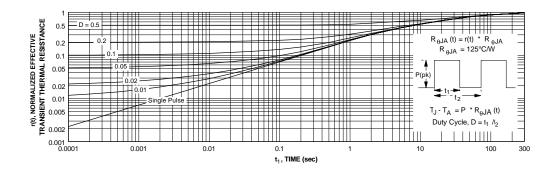
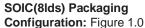


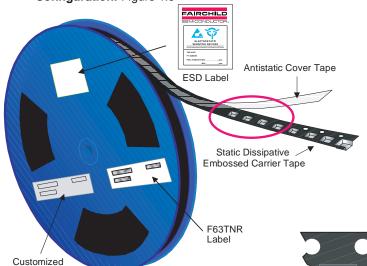
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

SO-8 Tape and Reel Data and Package Dimensions





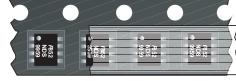


Packaging Description:

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SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and amit-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 300cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (antistatic coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reles are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.





Packaging Option Standard o flow code) L86Z D84Z Rail/Tube TNR Packaging type TNR TNR Qty per Reel/Tube/Bag 2.500 4.000 500 13" Dia 13" Dia 7" Dia 343y64y343 530x130x83 343y64y343 184v187v47 5,000 30,000 8,000 1,000

Box Dimension (mm) Max qty per Box Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

SOIC (8lds) Packaging Information

SOIC-8 Unit Orientation

F63TNR Label sample

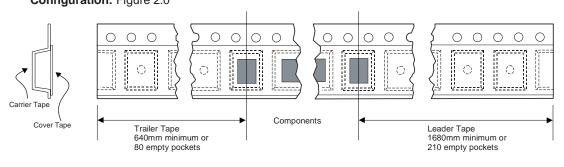
Label

Reel Size



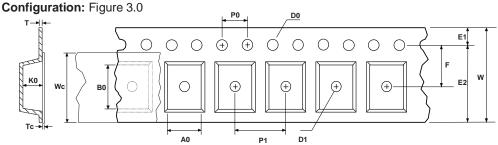
343mm x 342mm x 64mm Standard Intermediate box ESD Label F63TNL F63TN Label

SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0





SOIC(8lds) Embossed Carrier Tape



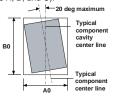


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

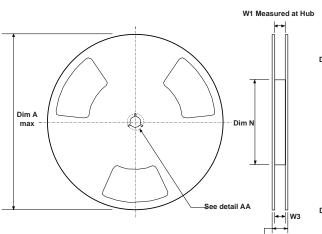
Component Rotation



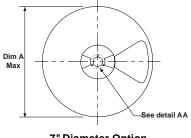
Sketch C (Top View)

Component lateral movement

SOIC(8lds) Reel Configuration: Figure 4.0



13" Diameter Option



7" Diameter Option

B Min

Dim C

Dim D

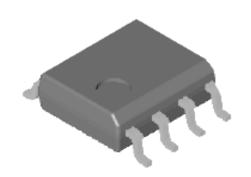
min

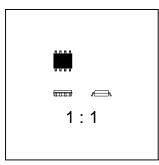
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

W2 max Measured at Hub

SO-8 Tape and Reel Data and Package Dimensions, continued

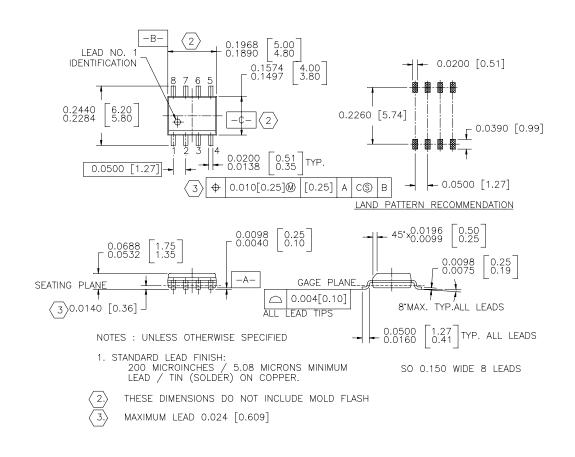
SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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 E^2CMOS^{TM} PowerTrenchTM

FACT™ QFET™ FACT Quiet Series™ QS™

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